

General Description

This device has been developed using Trench-technology these products have been designed to minimize on-state resistance and provides an extremely efficient for various power applications.

100V N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	ID
100 V	1.42m Ω @10 V	296 A

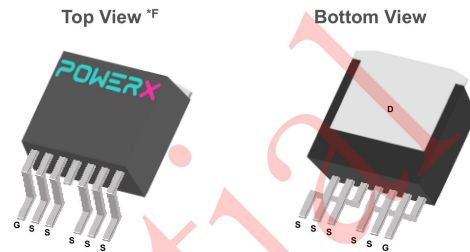
Features

- Very Low On-Resistance
- High Current Capability
- High UIS Rated
- RoHS Compliant and Halogen-free

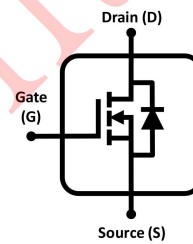
Applications

- Hot Swap and O-Ring
- Motor Drive
- BMS
- PV Inverter
- Power Rails

TO263-7



Pin Configuration



Absolute Maximum Ratings (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{DS}	Drain-Source Voltage	100	V	
V _{GS}	Gate-Source Voltage	±20		
I _D	Drain Current-Continuous ^{*A}	T _A =25 °C	34	A
		T _A =70 °C	27	
		T _C =25 °C	296	
		T _C =100 °C	187	
I _{DM}	Drain Current-Pulsed ^{*A,B}	T _A =25°C	700	A
I _{AS}	Non-repetitive Avalanche Current ^{*F}		116	A
E _{AS}	Single Pulse Drain-to-Source Avalanche Energy ^{*E}		673	mJ
P _D	Maximum Power Dissipation	T _A =25 °C	3.1	W
		T _C =25 °C	227	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C	

Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
R _{θJA}	Junction-to-Ambient ^{*C}	Steady State	40	°C/W
R _{θJC}	Junction-to-Case	Steady State	0.55	°C/W